



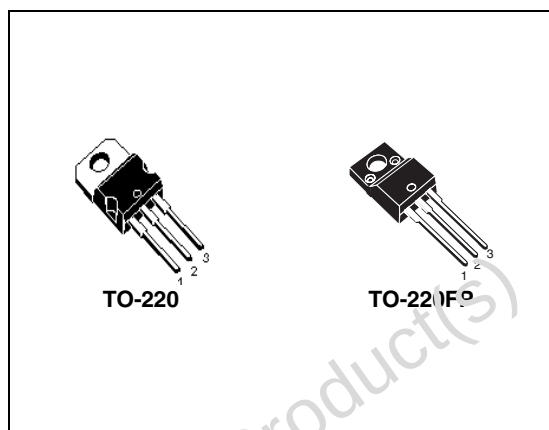
STP8NK85Z STF8NK85Z

N-channel 850V - 1.1Ω - 6.7A - TO-220 /TO-220FP
Zener - protected SuperMESH™ Power MOSFET

General features

Type	V _{DSS} (@T _{jmax})	R _{DS(on)}	I _D
STP8NK85Z	850 V	< 1.4 Ω	6.7 A
STF8NK85Z	850 V	< 1.4 Ω	6.7 A

- Extremely high dv/dt capability
- 100% avalanche tested
- Gate charge minimized
- Very low intrinsic capacitances
- Very good manufacturing repeatability



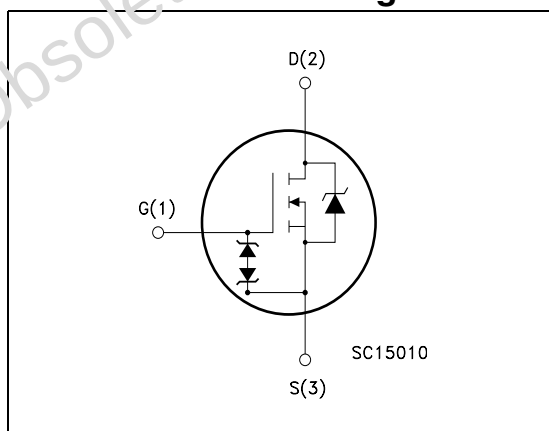
Description

The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage MOSFETs including revolutionary MDmesh™ products.

Applications

- Switching application

Internal schematic diagram



Order codes

Part number	Marking	Package	Packaging
STP8NK85Z	P8NK85Z	TO-220	Tube
STF8NK85Z	F8NK85Z	TO-220FP	Tube

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1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-220	TO-220FP	
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	850		V
V_{GS}	Gate- source voltage	± 30		V
I_D	Drain current (continuous) at $T_C = 25^\circ\text{C}$	6.7	6.7 ⁽¹⁾	A
I_D	Drain current (continuous) at $T_C = 100^\circ\text{C}$	4.3	4.3 ⁽¹⁾	A
$I_{DM}^{(2)}$	Drain current (pulsed)	26.7	26.7 ⁽¹⁾	A
P_{TOT}	Total dissipation at $T_C = 25^\circ\text{C}$	150	35	W
	Derating factor	1.20	0.28	W/ $^\circ\text{C}$
$V_{ESD(G-S)}$	Gate source ESD(HBM-C=100pF, R=1.5K Ω)	4000		V
$dv/dt^{(3)}$	Peak diode recovery voltage slope	4.5		V/ns
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink ($t=1\text{s}$; $T_C = 25^\circ\text{C}$)	-	2500	V
T_j T_{stg}	Max operating junction temperature Storage temperature	-55 to 150		$^\circ\text{C}$

- Limited only by maximum temperature allowed
- Pulse width limited by safe operating area
- $I_{SD} \leq 6.7\text{ A}$, $di/dt \leq 200\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_j \leq T_{JMAX}$.

Table 2. Thermal data

Symbol	Parameter	Value		Unit
		TO-220	TO-220FP	
$R_{thj-case}$	Thermal resistance junction-case max	0.83	3.6	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.5		$^\circ\text{C}/\text{W}$
T_I	Maximum lead temperature for soldering purpose	300		$^\circ\text{C}$

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by $T_j \text{ Max}$)	6.7	A
E_{AS}	Single pulse avalanche energy (starting $T_j=25^\circ\text{C}$, $I_d=I_{AR}$, $V_{dd}=50\text{V}$)	350	mJ

Table 4. Gate-source zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
BV_{GSO}	Gate-source breakdown voltage	$I_{GS}=\pm 1\text{mA}$ (Open Drain)	30			V

1.1 Protection features of gate-to-source zener diodes

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

2 Electrical characteristics

(T_{CASE}=25°C unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown voltage	I _D = 1mA, V _{GS} = 0	850			V
I _{DSS}	Zero Gate voltage Drain current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125°C			1 50	μA μA
I _{GSS}	Gate-body leakage Current (V _{DS} = 0)	V _{GS} = ± 20 V			± 10	μA
V _{GS(th)}	Gate threshold voltage	V _{DS} = V _{GS} , I _D = 100 μA	3	3.75	4.5	V
R _{DS(on)}	Static drain-source on resistance	V _{GS} = 10 V, I _D = 3.35 A		1.1	1.4	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g _{fs} ⁽¹⁾	Forward transconductance	V _{DS} = 15V, I _D = 3.35 A		6		S
C _{iss} C _{oss} C _{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V _{DS} = 25 V, f = 1 MHz, V _{GS} = 0		1870 190 44		pF pF pF
C _{oss eq.} ⁽²⁾	Equivalent output capacitance	V _{DS} = 0V, V _{DS} = 0V to 680V		75		pF
t _{d(on)} t _r t _{d(off)} t _f	Turn-on delay time Rise time Turn-off delay time Fall time	V _{DD} = 425 V, I _D = 3.35 A, R _G = 4.7 Ω, V _{GS} = 10 V (see Figure 18)		26 19 58 18		ns ns ns ns
t _{r(Voff)} t _r t _c	Off-voltage rise time Fall time Cross-over time	V _{DD} = 680 V, I _D = 6.7 A, R _G = 4.7 Ω, V _{GS} = 10 V (see Figure 20)		12 10 24		ns ns ns
Q _g Q _{gs} Q _{gd}	Total gate charge Gate-source charge Gate-drain charge	V _{DD} = 680 V, I _D = 6.7 A, V _{GS} = 10 V (see Figure 19)		60 12 35	84	nC nC nC

1. Pulsed: pulse duration=300μs, duty cycle 1.5%

2. C_{oss eq.} is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current				6.7	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				26.7	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 6.7 \text{ A}$, $V_{GS} = 0$			1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 6.7 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$		530		ns
Q_{rr}	Reverse Recovery Charge	$V_{DD} = 35 \text{ V}$, $T_j = 25^\circ\text{C}$		4.5		μC
I_{RRM}	Reverse Recovery Current	(see Figure 20)		17		A
t_{rr}	Reverse recovery time	$I_{SD} = 6.7 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$		690		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 35 \text{ V}$, $T_j = 150^\circ\text{C}$		6.4		μC
I_{RRM}	Reverse recovery current	(see Figure 20)		17		A

1. Pulsed: pulse duration=300 μs , duty cycle 1.5%

2. Pulse width limited by safe operating area

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area for TO-220

Figure 2. Thermal impedance for TO-220

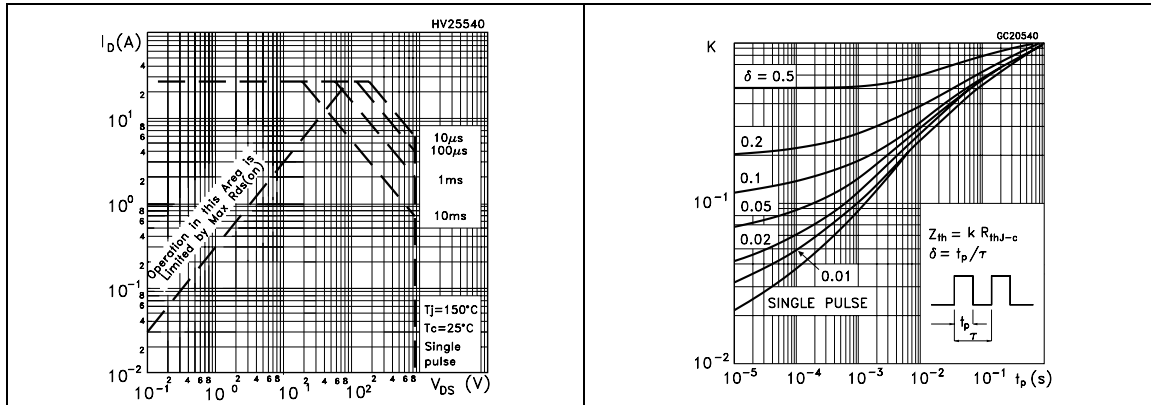


Figure 3. Safe operating area for TO-220FP

Figure 4. Thermal impedance for TO-220FP

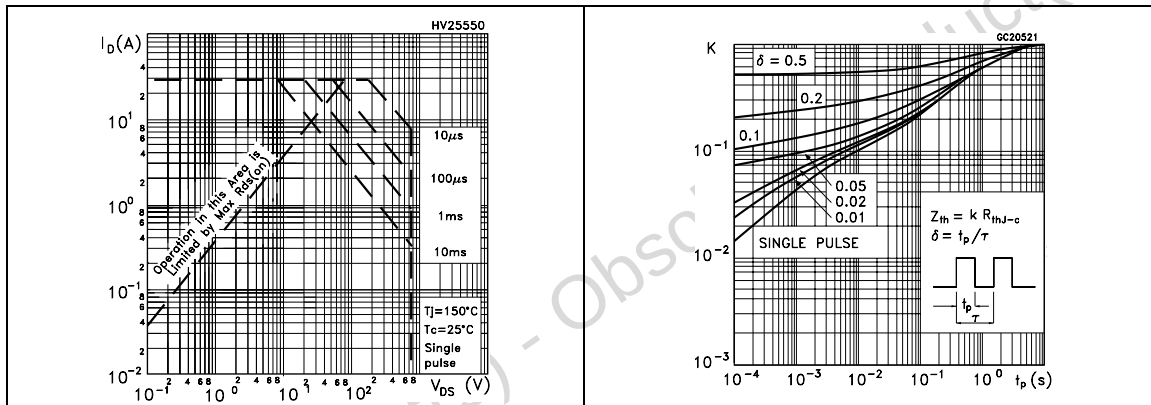


Figure 5. Output characteristics

Figure 6. Transfer characteristics

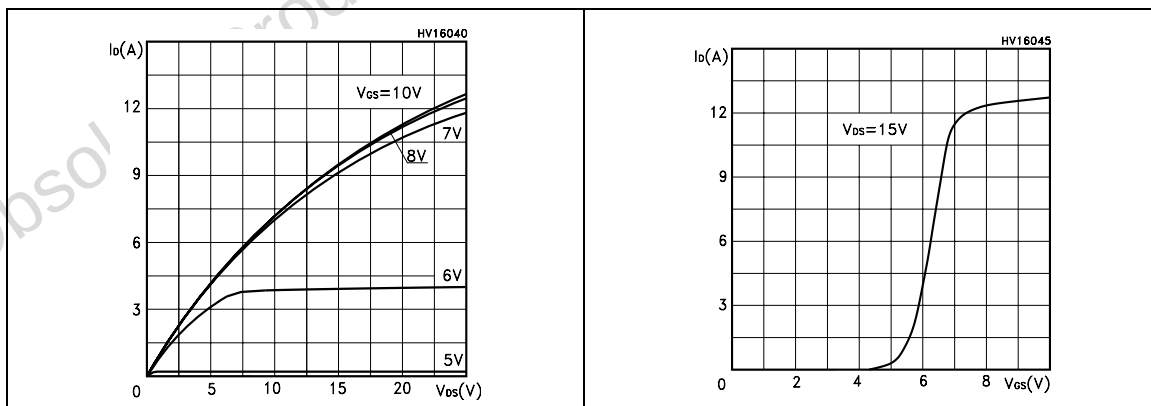


Figure 7. Transconductance

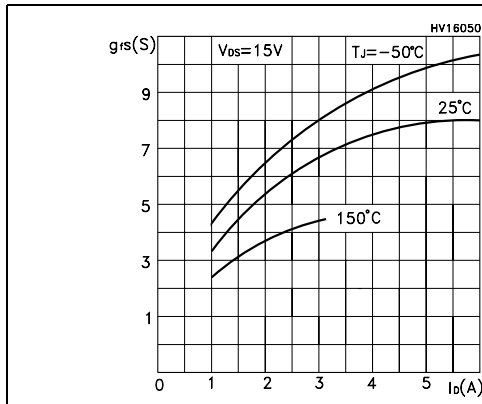


Figure 8. Static drain-source on resistance

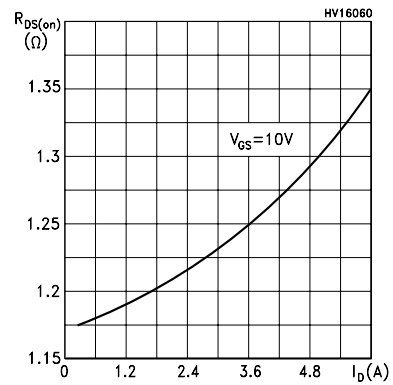


Figure 9. Gate charge vs gate-source voltage

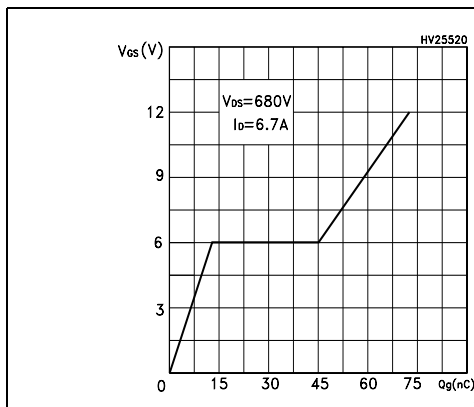


Figure 10. Capacitance variations

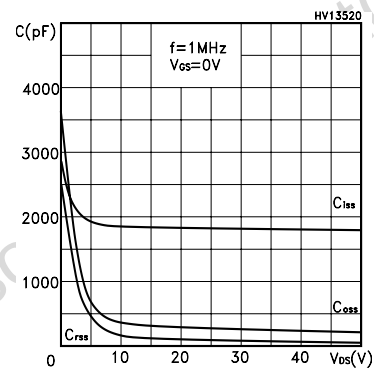


Figure 11. Normalized gate threshold voltage vs temperature

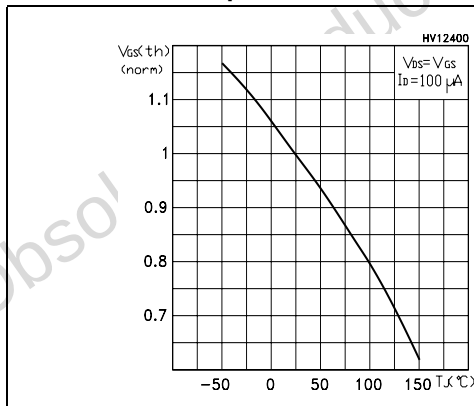
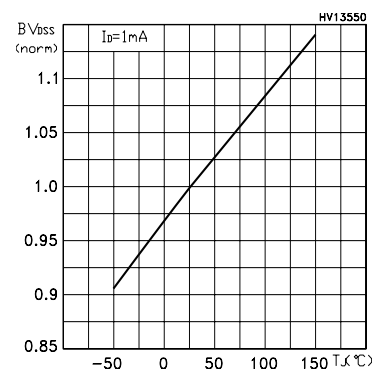
Figure 12. Normalized B_{VDS} vs Temperature

Figure 13. Normalized on resistance vs temperature

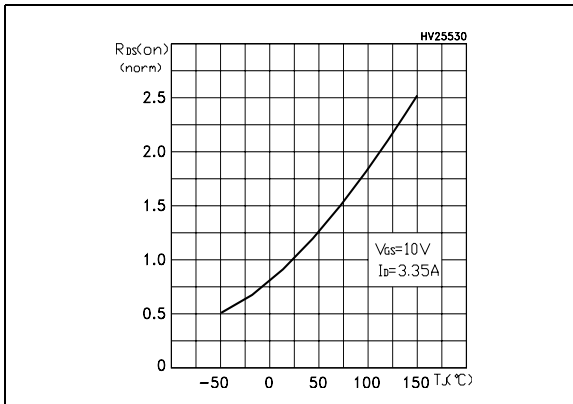


Figure 14. Source-drain diode forward characteristic

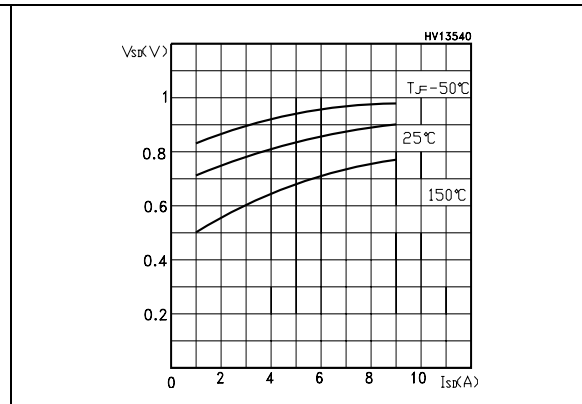
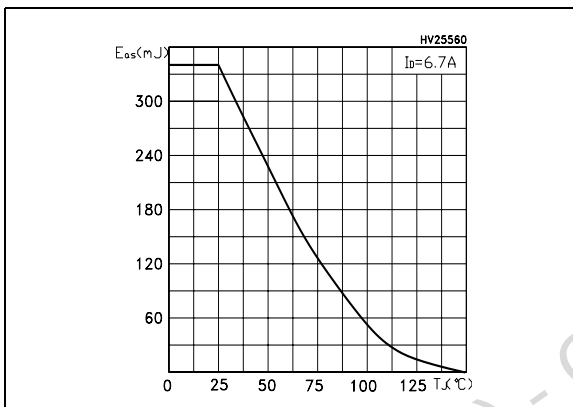


Figure 15. Avalanche energy vs temperature



3 Test circuit

Figure 16. Unclamped inductive load test circuit

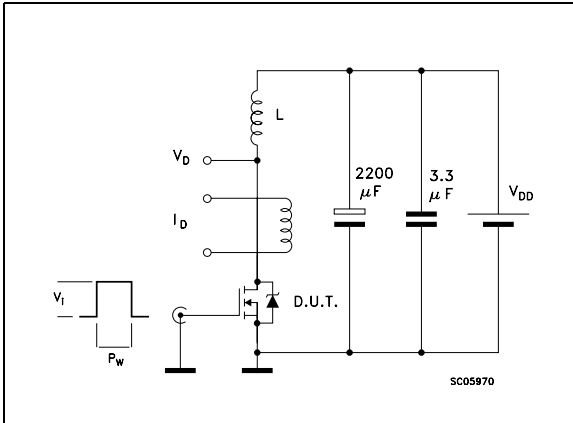


Figure 17. Unclamped inductive waveform

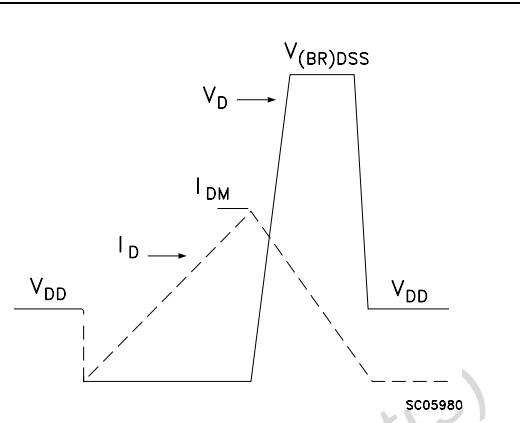


Figure 18. Switching times test circuit for resistive load

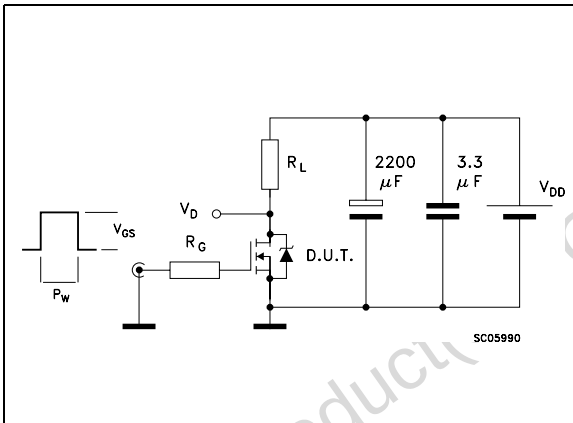


Figure 19. Gate charge test circuit

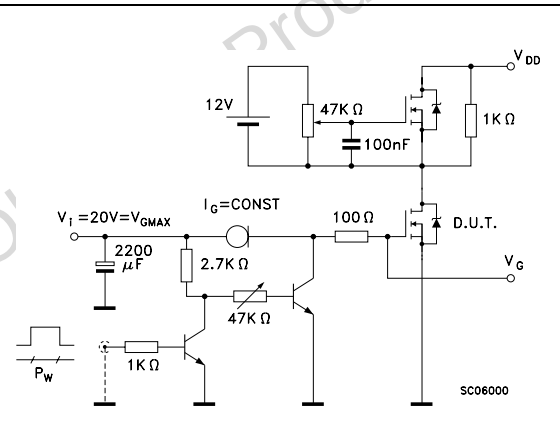
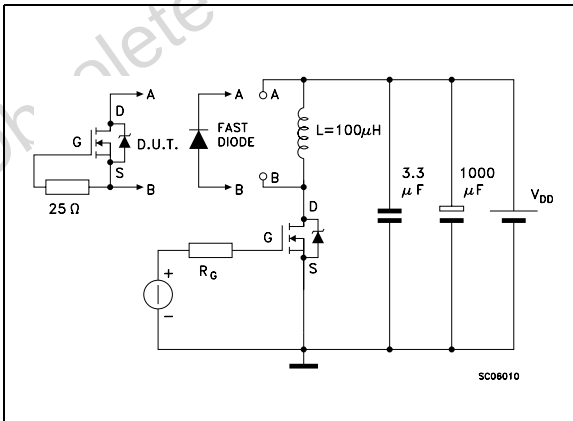


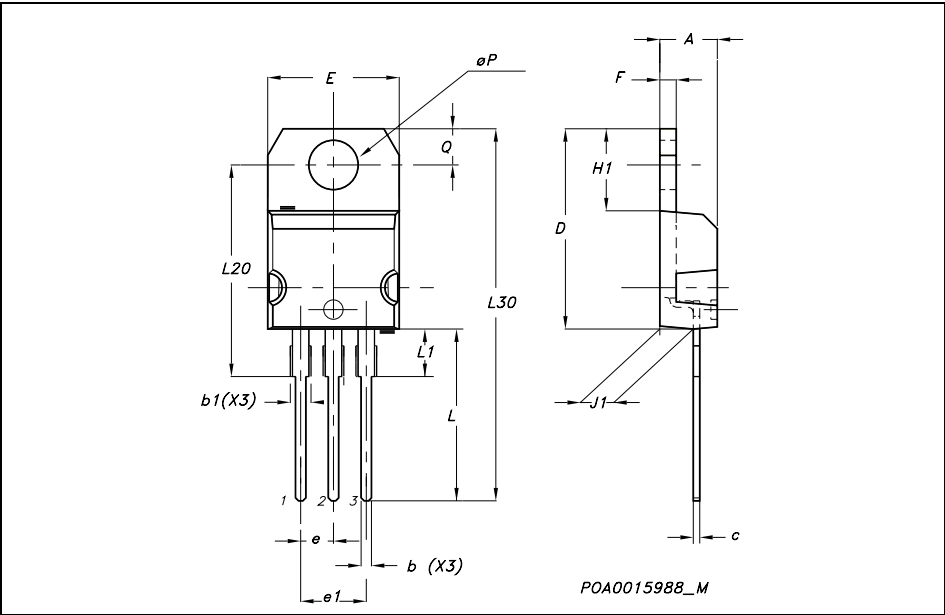
Figure 20. Test circuit for inductive load switching and diode recovery times



4 Package mechanical data

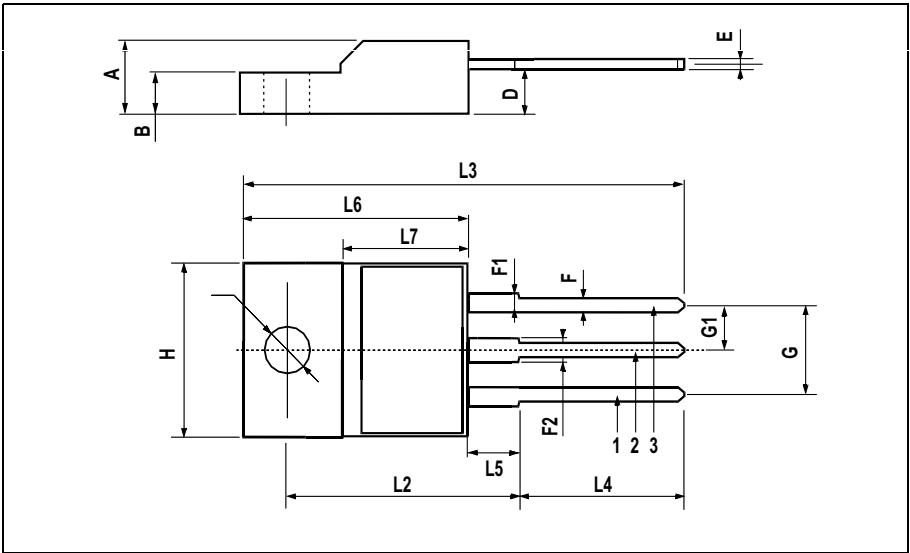
In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

TO-220 MECHANICAL DATA						
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



TO-220FP MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



5 Revision history

Table 8. Revision history

Date	Revision	Changes
02-Mar-2005	1	First release
16-May-2005	2	Modified value in table 7
08-Sep-2005	3	Final datasheet
09-Feb-2006	4	ECOPACK label
20-Sep-2006	5	New template, no content change

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